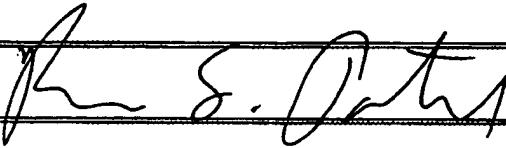


FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 05-720-US2	Serial No. 10/559,981
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)			
<b>Applicant:</b> Kouvettakis, et al.			
<b>Filing Date:</b> December 8, 2005 <b>Group:</b> 2812			

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RSP	70.	R. Gaska, A. Zukauskas, M. S. Shur, and M. A. Khan, "Progress in III-nitride based white light sources", Proceedings of the SPIE, Vol: 4776, pp. 82-96 (2002).
	71.	R. Bauer, C. Ritter, P. Crozier, J. Menendez, J. Ren, and J. Kouvettakis, "Synthesis of ternary Si-Ge-Sn semiconductors on Si(100) via Sn <sub>x</sub> Ge <sub>1-x</sub> buffer layers", Appl. Phys. Lett. 83 (11), 2163-2165 (2003).
	72.	H.K. Shin, D.J. Lockwood, J.-M. Baribeau, "Strain in coherent-wave SiGe/Si superlattices", Solid State Commun., Vol: 114(10), pp. 505-510 (2000).
	73.	M. Meléndez-Lira, J. D. Lorentzen, J. Menéndez, W. Windl, N. Cave, R. Liu, J. W. Christiansen, N. D. Theodore, and J. J. Candelaria, "Microscopic carbon distribution in Si <sub>1-x</sub> C <sub>x</sub> alloys: A Raman scattering study", Phys. Rev. B 56, pp. 3648-3650 (1997).
	74.	C.S. Cook, S. Zollner, M.R. Bauer, P. Aella, J. Kouvettakis, and J. Menendez, "Optical constants and interband transitions of Ge <sub>1-x</sub> Sn <sub>x</sub> alloys (x < 0.2) grown on Si by UHV-CVD", Thin Solid Films 455-456, pp. 217-221 (2004).
	75.	Chizmeshya, et al., "Experimental and Theoretical study of deviations from Vegards Law in the Ge <sub>1-x</sub> Ge <sub>1-x</sub> system", Chem. Of Malls., Vol: 15, pp. 2511-2519 (2003).
	76.	Aella, et al., "Structural and optical properties of Sn <sub>x</sub> Si <sub>1-x</sub> Ge <sub>1-x-y</sub> alloys", App. Phys. Lett. Vol: 84, pp. 888-890 (2004).
	77.	Roucka, et al., "Versatile buffer layer architectures based on Ge <sub>1-x</sub> Sn <sub>x</sub> alloys", Appl. Phys. Let. Vol: 86(19), pp. 191912-191914 (2005).
	78.	He, et al., "Synthesis of epitaxial Sn <sub>x</sub> Ge <sub>1-x</sub> alloy films by ion-assisted molecular beam epitaxy", App. Phys. Lett., Vol: 68(5), pp. 664-666 (1996). <del>Pristovsek, et al., "Growth of strained gaAsSb layers on GaAs (001) by MOVPE", Journal of Crystal Growth, Vol: 276, pp. 347-353 (2005).</del>
✓	79.	Pristovsek, et al., "Growth of strained gaAsSb layers on GaAs (001) by MOVPE", Journal of Crystal Growth, Vol: 276, pp. 347-353 (2005).

EXAMINER		DATE CONSIDERED	4/19/07
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